www.vishay.com

Vishay Semiconductors

Power Rectifiers Diodes (T-modules), 40 A to 110 A



D-55 (T-module)

| PRIMARY CHARACTERISTICS | | | | | | | |
|-------------------------|-------------------------------|--|--|--|--|--|--|
| I _{F(AV)} | 40 A to 110 A | | | | | | |
| Туре | Modules - diode, high voltage | | | | | | |
| V_{RRM} | 100 V to 1200 V | | | | | | |
| Package | D-55 (T-module) | | | | | | |
| Circuit configuration | Single diode | | | | | | |

FEATURES

- · Electrically isolated base plate
- Types up to 1200 V_{RRM}
- 3500 V_{RMS} isolating voltage
- · Simplified mechanical designs, rapid assembly
- High surge capability
- Large creepage distances
- UL E78996 approved
- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

These series of T-modules use standard recovery power rectifier diodes. The semiconductors are electrically isolated from the metal base, allowing common heatsink and compact assembly to be built.

Applications include power supplies, battery charges, welders, motor controls and general industrial current rectification.

| MAJOR RA | MAJOR RATINGS AND CHARACTERISTICS | | | | | | |
|---------------------|-----------------------------------|-------------|--------|---------|---------|-------------------|--|
| SYMBOL | CHARACTERISTICS | T40HF | T70HF | T85HF | T110HF | UNITS | |
| 1 | | 40 | 70 | 85 | 110 | Α | |
| I _{F(AV)} | T _C | 85 | 85 | 85 | 85 | °C | |
| I _{F(RMS)} | | 63 | 110 | 134 | 173 | Α | |
| 1 | 50 Hz | 570 | 1200 | 1700 | 2000 | А | |
| I _{FSM} | 60 Hz | 600 | 1250 | 1800 | 2100 | | |
| l ² t | 50 Hz | 1630 | 7100 | 14 500 | 20 500 | A ² s | |
| 1-1 | 60 Hz | 1500 | 6450 | 13 500 | 18 600 | A-S | |
| I ² √t | | 16 300 | 70 700 | 148 700 | 204 300 | A ² √s | |
| V _{RRM} | | 100 to 1200 | | | | V | |
| T _J | | | -40 to | +150 | | °C | |

ELECTRICAL SPECIFICATIONS

| VOLTAGE R | VOLTAGE RATINGS | | | | | | | | | |
|----------------------|-----------------|--|--|---|--|--|--|--|--|--|
| TYPE NUMBER | VOLTAGE CODE | V _{RRM} , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V | V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V | I _{RRM} MAXIMUM AT T _J = 25 °C μA | | | | | | |
| | 10 | 100 | 150 | | | | | | | |
| | 20 | 200 | 300 | | | | | | | |
| VS-T40HF | 40 | 400 | 500 | | | | | | | |
| VS-T70HF VS-T85HF | 60 | 600 | 700 | 100 | | | | | | |
| VS-T03FIF | 80 | 800 | 900 | | | | | | | |
| | 100 | 1000 | 1100 | | | | | | | |
| | 120 | 1200 | 1300 | | | | | | | |



Vishay Semiconductors

| FORWARD CONDUCTION | | | | | | | | | |
|---|---------------------|--|--|---------------------------------------|--------|--------|----------------|---------|------------------|
| DADAMETED | OVALDOL | | TEST SONDITI | IONO | | VA | LUES | | |
| PARAMETER | SYMBOL | | TEST CONDITI | ONS | T40HF | T70HF | T85HF | T110HF | UNITS |
| Maximum average forward | I _{F(AV)} | 180° condu | 180° conduction, half sine wave | | | 70 | 85 | 110 | Α |
| current at case temperature | ·F(AV) | | | | 85 | 85 | 85 | 85 | °C |
| Maximum RMS forward current | I _{F(RMS)} | | | | 63 | 110 | 134 | 173 | Α |
| Maximum neak and avala | | t = 10 ms | No voltage | | 570 | 1200 | 1700 | 2000 | |
| Maximum peak, one-cycle forward, non-repetitive surge | l= | t = 8.3 ms | reapplied | | 600 | 1250 | 1800 | 2100 | Α |
| current | I _{FSM} | t = 10 ms | 100 % V _{RRM} | Sinusoidal | 480 | 1000 | 1450 | 1700 | |
| Current | | t = 8.3 ms | reapplied | half wave, | 500 | 1050 | 1500 | 1780 | |
| | | t = 10 ms | No voltage | initial $T_J =$ | 1630 | 7100 | 14 500 | 20 500 | A ² s |
| Mar. 120 121 fact fraise | l ² t | t = 8.3 ms | reapplied | T _J maximum | 1500 | 6450 | 6450 13 500 18 | 18 600 | |
| Maximum I ² t for fusing | 1-1 | t = 10 ms 100 % V _{RRM} | 1150 | 5000 | 10 500 | 14 500 | A-S | | |
| | | t = 8.3 ms | reapplied | | 1050 | 4570 | 9600 | 13 200 | |
| Maximum l²√t for fusing | I²√t | t = 0.1 ms t | to 10 ms, no volt | tage reapplied | 16 300 | 70 700 | 148 700 | 204 300 | A²√s |
| Low level value of threshold voltage | V _{F(TO)1} | (16.7 % x π T _J maximu | $\mathbf{x} \times \mathbf{I}_{F(AV)} < \mathbf{I} < \pi \times \mathbf{X}$ | I _{F(AV)}), | 0.66 | 0.76 | 0.68 | 0.68 | V |
| High level value of threshold voltage | V _{F(TO)2} | $(I > \pi \times I_{F(A)})$ | $(I > \pi \times I_{F(AV)}), T_J$ maximum | | | 0.95 | 0.90 | 0.86 | V |
| Low level value of forward slope resistance | r _{f1} | (16.7 % x π x $I_{F(AV)}$ < I < π x $I_{F(AV)}$), I_{J} maximum | | | 4.3 | 2.4 | 1.76 | 1.56 | 0 |
| High level value of forward slope resistance | r _{f2} | $(I > \pi \times I_{F(AV)}), T_J$ maximum | | | 3.1 | 1.7 | 1.08 | 1.12 | mΩ |
| Maximum forward voltage drop | V _{FM} | $t_p = 400 \ \mu s$ | $_{(AV)}$, $T_J = 25 ^{\circ}C$, square pulse ower = $V_{F(TO)} \times I_F$ | $_{(AV)} + r_f \times (I_{F(RMS)})^2$ | 1.30 | 1.35 | 1.27 | 1.35 | V |

| BLOCKING | | | | | | | |
|--------------------------------------|-------------------|--|-------|-------|-------|--------|-------|
| PARAMETER | SYMBOL | TEST CONDITIONS | T40HF | T70HF | T85HF | T110HF | UNITS |
| Maximum peak reverse leakage current | I _{RRM} | T _J = 150 °C | 15 | 15 | 20 | 20 | mA |
| RMS isolation voltage | V _{ISOL} | 50 Hz, circuit to base, all terminals shorted $T_J = 25$ °C, $t = 1$ s | 3500 | 3500 | 3500 | 3500 | V |

| THERMAL AND MECHANICAL SPECIFICATIONS | | | | | | | | |
|---|-----------------------------------|---|------------|----------------|--------|----------|--------|-------|
| PARAMETER | SYMBOL | TEST | CONDITIONS | | VAL | .UES | | UNITS |
| PANAMETER | STWIBOL | 1231 | CONDITIONS | T40HF | T70HF | T85HF | T110HF | UNITS |
| Maximum junction operating and storage temperature range | T _J , T _{Stg} | | | | -40 to | +150 | | °C |
| Maximum thermal resistance, junction to case per junction | R _{thJC} | DC operation | 1.36 | 0.69 | 0.62 | 0.47 | K/W | |
| Maximum thermal resistance, case to heatsink | R _{thCS} | Mounting surface smooth, flat and greased 0.2 | | | | | r∨ vv | |
| Mounting torque, to heatsink | | Non-lubricated M3.5 mounting screws (1) | | (1) 1.3 ± 10 % | | | | Nm |
| ± 10 % terminals | | threads M5 screw terminals | | 3 ± 10 % | | | INIII | |
| Approximate weight | | See dimensions - link at the end of datasheet | | t 54 | | | • | g |
| Case style | | | | | D- | 55 (T-mc | dule) | |

Note

⁽¹⁾ A mounting compound is recommended and the torque should be rechecked after a period of about 3 hours to allow for the spread of the compound

www.vishay.com

Vishay Semiconductors

| ∆R CONDUC | CTION P | ER JUN | CTION | | | | | | | | |
|-----------|---------|----------|----------|----------------------|-------|-------|----------|----------|------------------------|--------|-------|
| DEVICES | SINUS | DIDAL CO | NDUCTION | AT T _J MA | XIMUM | RECTA | NGULAR C | ONDUCTIO | N AT T _J MA | AXIMUM | UNITS |
| DEVICES | 180° | 120° | 90° | 60° | 30° | 180° | 120° | 90° | 60° | 30° | UNITS |
| T40HF | 0.12 | 0.14 | 0.18 | 0.27 | 0.46 | 0.09 | 0.15 | 0.20 | 0.28 | 0.46 | |
| T70HF | 0.09 | 0.11 | 0.14 | 0.20 | 0.35 | 0.07 | 0.11 | 0.15 | 0.21 | 0.35 | K/W |
| T85HF | 0.08 | 0.09 | 0.12 | 0.18 | 0.31 | 0.06 | 0.10 | 0.13 | 0.19 | 0.31 | IV VV |
| T110HF | 0.05 | 0.07 | 0.09 | 0.14 | 0.23 | 0.05 | 0.08 | 0.10 | 0.15 | 0.24 | |

Note

• Table shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

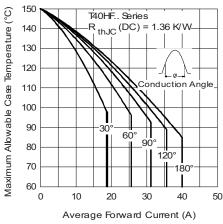


Fig. 1 - Current Ratings Characteristics

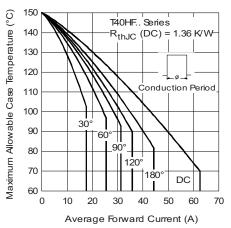


Fig. 2 - Current Ratings Characteristics

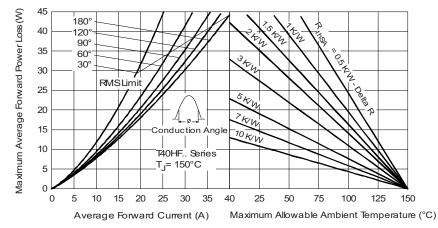


Fig. 3 - Forward Power Loss Characteristics

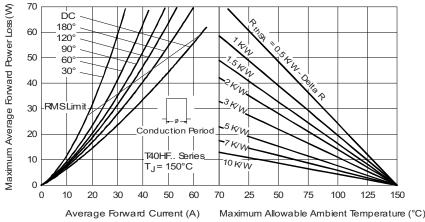


Fig. 4 - Forward Power Loss Characteristics

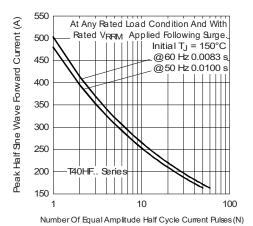


Fig. 5 - Maximum Non-Repetitive Surge Current

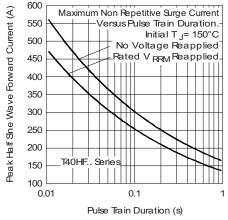


Fig. 6 - Maximum Non-Repetitive Surge Current

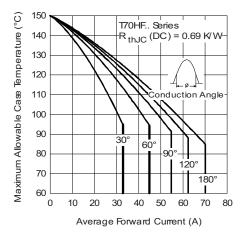


Fig. 7 - Current Ratings Characteristics

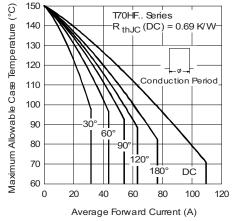


Fig. 8 - Current Ratings Characteristics

www.vishay.com

Vishay Semiconductors

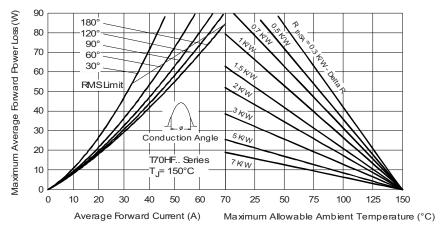


Fig. 9 - Forward Power Loss Characteristics

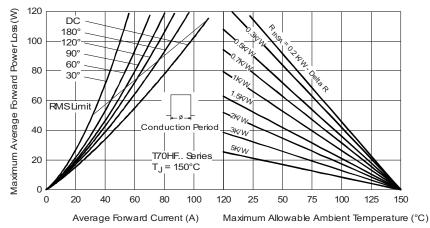


Fig. 10 - Forward Power Loss Characteristics

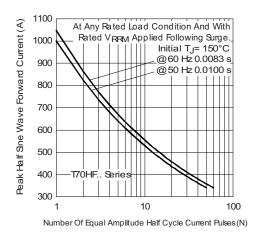


Fig. 11 - Maximum Non-Repetitive Surge Current

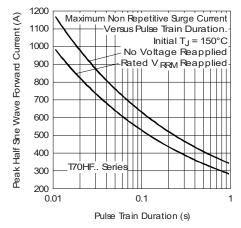


Fig. 12 - Maximum Non-Repetitive Surge Current

www.vishay.com

Vishay Semiconductors

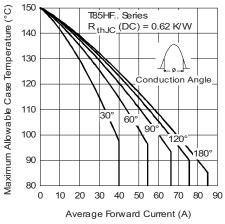


Fig. 13 - Current Ratings Characteristics

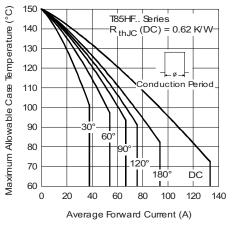


Fig. 14 - Current Ratings Characteristics

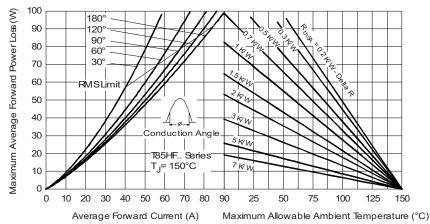


Fig. 15 - Forward Power Loss Characteristics

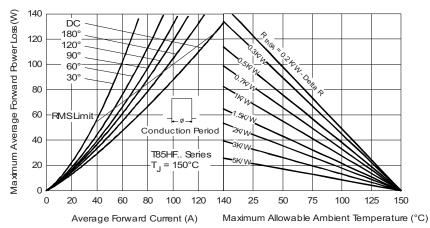


Fig. 16 - Forward Power Loss Characteristics

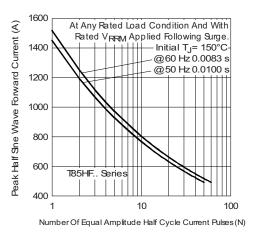


Fig. 17 - Maximum Non-Repetitive Surge Current

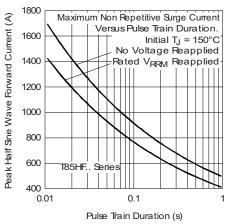


Fig. 18 - Maximum Non-Repetitive Surge Current

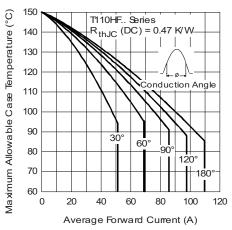


Fig. 19 - Current Ratings Characteristics

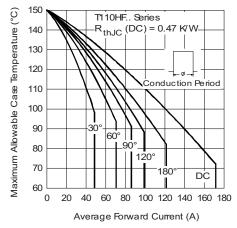


Fig. 20 - Current Ratings Characteristics

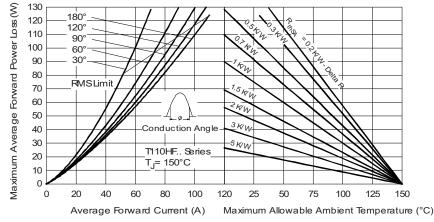


Fig. 21 - Forward Power Loss Characteristics

Vishay Semiconductors

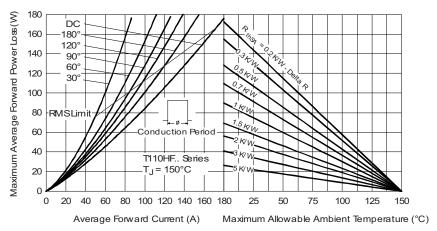


Fig. 22 - Forward Power Loss Characteristics

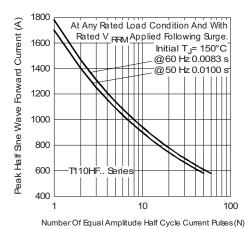


Fig. 23 - Maximum Non-Repetitive Surge Current

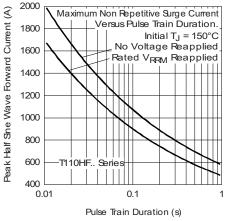


Fig. 24 - Maximum Non-Repetitive Surge Current

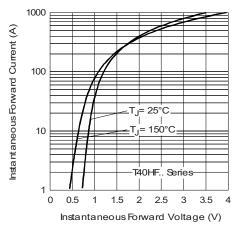


Fig. 25 - Forward Voltage Drop Characteristics

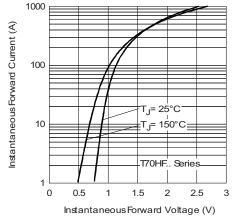


Fig. 26 - Forward Voltage Drop Characteristics

www.vishay.com

Vishay Semiconductors

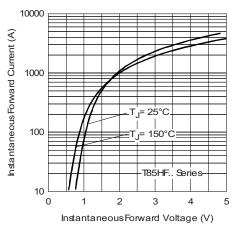


Fig. 27 - Forward Voltage Drop Characteristics

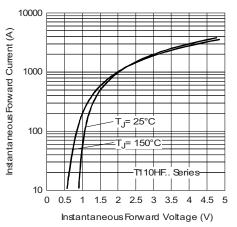


Fig. 28 - Forward Voltage Drop Characteristics

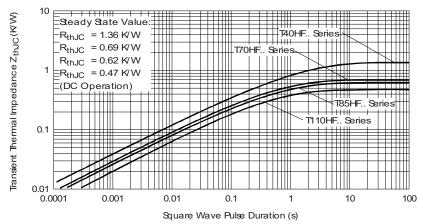


Fig. 29 - Thermal Impedance Z_{thJC} Characteristics

ORDERING INFORMATION TABLE

Device code

VST
110
HF
120

1 2 3 4 5

1 - Vishay Semiconductors product
2 - Module type
3 - Current rating
4 - Circuit configuration (see Circuit Configuration table)
5 - Voltage code x 10 = V_{RRM}

| CIRCUIT CONFIGURATION | | | | | | | | | |
|-----------------------|----------------------------|-----------------|--|--|--|--|--|--|--|
| CIRCUIT DESCRIPTION | CIRCUIT CONFIGURATION CODE | CIRCUIT DRAWING | | | | | | | |
| Single diode | HF | 2 0 0 1 | | | | | | | |

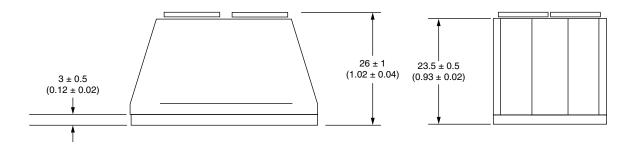
| LINKS TO RELAT | ED DOCUMENTS |
|----------------|--------------------------|
| Dimensions | www.vishay.com/doc?95313 |

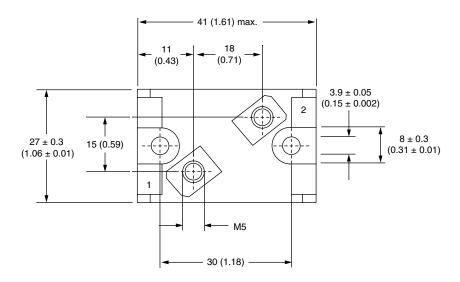


Vishay Semiconductors

D-55 T-Module Diode Standard and Fast Recovery

DIMENSIONS in millimeters (inches)





Note

• 1 = Anode 2 = Cathode



Legal Disclaimer Notice

Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.